L	Hits	Search Text	DB	Time stamp
Number				
	44	Gan same (gaas or gallium adj arsenide) near5 substrate and 117/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:32
_	28	Gan same (gaas or gallium adj arsenide) near5 substrate and 117/\$.ccls. and remov\$4 near4 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:23
_	3	("4622083" "4727047" "4931132").PN.	USPAT	2003/08/28 16:27
-	63	Gan near5 single same remov\$4 near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:38
-	131	117/915.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:44
-	13	117/915.ccls. and (gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28
_	19	117/915.ccls. and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 13:13
_	2	20020028314.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:13
_	95	((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate) near10 (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:18
-	141	(gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29
_	23	((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)) and 117\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:21
_	38	(((gaas or gallium near3 arsenide) near15 (sapphire or "al.sub.2o.sub.3") near5 substrate) same (gallium adj nitride or gan)) and 117\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:26
-	9	sacrific\$4 near5 substrate near10 sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:44
-	84	sacrific\$4 near5 substrate near10 (gaas or gallium near3 arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:54

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-	169		USPAT;	2003/08/29
		gallium near3 arsenide) or (sapphire or	US-PGPUB;	13:54
		"al.sub.2o.sub.3")) same (gallium adj	EPO; JPO;	
		nitride or gan)	DERWENT;	
			IBM_TDB	
-	122		USPAT;	2003/08/29
		(sapphire or "al.sub.2o.sub.3") near5	US-PGPUB;	13:54
		substrate same (gallium adj nitride or	EPO; JPO;	
		gan)) and 117\$.ccls.) (((gaas or gallium	DERWENT;	
		near3 arsenide) near15 (sapphire or	IBM_TDB	
		"al.sub.2o.sub.3") near5 substrate) same		
		(gallium adj nitride or gan)) and 117\$.ccls.) (sacrific\$4 near5 substrate		
		near10 (gaas or gallium near3 arsenide))		
	156		USPAT;	2003/08/29
1 -	130	gallium near3 arsenide) or (sapphire or	US-PGPUB;	15:06
		"al.sub.20.sub.3")) same (gallium adj	EPO; JPO;	13.00
		nitride or gan)) not ((((gaas or gallium	DERWENT;	
		near3 arsenide) near5 (sapphire or	IBM TDB	
		"al.sub.20.sub.3") near5 substrate same		
		(gallium adj nitride or gan)) and		
		117\$.ccls.) ((((gaas or gallium near3		
		arsenide) near15 (sapphire or		
		"al.sub.2o.sub.3") near5 substrate) same		
		(gallium adj nitride or gan)) and		
		117\$.ccls.) (sacrific\$4 near5 substrate		
		near10 (gaas or gallium near3 arsenide)))		